

AMENDMENTS TO THE CLAIMS:

Please amend the claims as follows:

1. (Currently Amended) A method for manufacturing a contact plug of a semiconductor device, the method comprising:
 - forming a wordline pattern ~~having~~ with a sequentially stacked structure of a wordline conductive material and a hard mask nitride film on a semiconductor substrate;
 - forming a ~~nitride film~~ spacer on a side of the wordline pattern;
 - forming a planarized interlayer insulating film covering the resultant structure ~~on the wordline pattern~~;
 - selectively etching the interlayer insulating film to form a contact hole;
 - forming a polysilicon layer on the entire surface of the resultant structure ~~surface of the interlayer insulating film where the contact hole is formed~~; and
 - performing a chemical mechanical polishing (CMP) process on the polysilicon layer ~~and the interlayer insulating film~~ resultant structure until the word line pattern ~~hard mask nitride film~~ is exposed using an acidic oxide film CMP slurry ~~on the polysilicon layer and interlayer insulating film, the acidic oxide film CMP slurry, wherein the slurry having~~ has a pH ranging from 2 to 7 and ~~containing~~ contains an oxidizer selected from the group consisting of hydrogen peroxide (H_2O_2), periodic acid (H_5IO_6), ferric nitrate [$Fe(N_3O_9)$] and combination combinations thereof ~~until the hard mask nitride film is exposed, making the etching ratio between polysilicon and interlayer insulating film substantially same.~~
2. (Canceled)
3. (Original) The method according to claim 1, wherein the oxidizer is present in an amount ranging from 1 to 40 vol% based on the CMP slurry.

4. (Original) The method according to claim 1, wherein the oxidizer is present in an amount ranging from 20 to 30 vol% based on the CMP slurry.

5. (Original) The method according to claim 1, wherein the acidic slurry has pH ranging from 2 to 5.

6. (Currently Amended) The method according to claim 1, wherein the acidic slurry comprises an abrasive selected from the group consisting of silica (SiO_2), ceria (CeO_2), zirconia (ZrO_2), alumina (Al_2O_3), and ~~combination~~ combinations thereof.

7. (Original) The method according to claim 6, wherein the abrasive is present in an amount ranging from 10 to 50 wt% based on the CMP slurry.

8. (Original) The method according to claim 7, wherein the abrasive is present in an amount ranging from 25 to 35 wt% based on the CMP slurry.

9. (Original) The method according to claim 1, wherein the polysilicon layer is formed using one selected from the group consisting of P-doped amorphous silicon film, P-doped polysilicon film, P-doped epitaxial silicon film, and combinations thereof.

10. (Canceled)

11. (Original) The method according to claim 1, wherein the interlayer insulating film is formed of a BPSG (borophosphosilicate glass) or HDP (high density plasma) oxide film.

12. (Currently Amended) A method for manufacturing a contact plug of a semiconductor device, the method comprising:

forming a wordline pattern ~~having~~ with a sequentially stacked of a wordline conductive material and a hard mask nitride film on a semiconductor substrate;

forming a ~~nitride film~~ spacer on a side of the wordline pattern;

forming a planarized interlayer insulating film covering the resultant structure on the wordline pattern;

selectively etching the interlayer insulating film on a partial region ~~until the substrate is exposed~~ to form a contact hole;

forming a polysilicon layer on the entire surface of the resultant structure ~~surface of the interlayer insulating film where the contact hole is formed~~; and

performing a chemical mechanical polishing CMP process on the resultant structure until the wordline pattern is exposed ~~the polysilicon layer and the interlayer insulating film~~ using an acidic oxide film CMP slurry ~~on the polysilicon layer and the interlayer insulating film~~, wherein the acidic oxide film CMP slurry having has [[a]] pH ranging 2 to 7 containing and contains H₂O₂ in an amount ranging from 1 to 40 vol%, making the etching ratio between polysilicon and interlayer insulating film substantially same.

13. (Previously Presented) The method according to claim 12, wherein the H₂O₂ is present in an amount ranging from 20 to 30 vol% based on the CMP slurry.

14. (Original) The method according to claim 12, wherein the acidic slurry has a pH ranging from 2 to 5.

15. (Original) The method according to claim 12, wherein the acidic slurry comprises an abrasive selected from the group consisting of silica (SiO_2), ceria (CeO_2), zirconia (ZrO_2), alumina (Al_2O_3), and combinations thereof.
16. (Original) The method according to claim 15, wherein the abrasive is present in an amount ranging from 10 to 50 wt% based on the CMP slurry.
17. (Original) The method according to claim 15, wherein the abrasive is present in an amount ranging from 25 to 35 wt% based on the CMP slurry.
18. (Original) The method according to claim 12, wherein the polysilicon layer is formed using one selected from the group consisting of P-doped amorphous silicon film, P-doped polysilicon film, P-doped epitaxial silicon film, and combinations thereof.
19. (Original) The method according to claim 12, wherein the wordline conductive material is formed of a SiON or organic bottom ARC layer.
20. (Original) The method according to claim 12, wherein the interlayer insulating film is formed of a BPSG (borophosphosilicate glass) or HDP (high density plasma) oxide film.